AMENDMENTS TO THE CLAIMS

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (Original) A method of manufacturing an integrated circuit transformer comprising:

forming a first metallization layer on a substrate comprising a first plurality of turns of a first winding:

forming an insulating layer over said first metallization layer;

forming a second metallization layer on said insulating layer comprising a second plurality of turns of a second winding, and a third plurality of turns of a third windings; and

connecting one end of said second winding to one end of said first winding whereby a primary winding is provided for said transformer and said third winding comprises a secondary for said transformer.

5. (Original) The method according to claim 4 further comprising forming a via in said insulating layer and connecting said one end of said second winding to said one end of said first winding through said via.

6. (Original) The method according to claim 4 wherein said second plurality of turns of said second winding are separated by said third plurality of turns of said third winding.

7. (Original) The method according to claim 4 further comprising:

forming a fourth set of a plurality of turns of a fourth winding on said first metallization layer to form a second secondary winding for said transformer.

8. (Original) The method according to claim 7 wherein each turn of said fourth winding is separated from each other by said first plurality of turns of said transformer winding.

9. (Original) The method according to claim 4 comprising:

forming an insulating layer over a region of a substrate having semiconductor devices; and

forming said first metallization layer on said insulating layer.

10. (Original) The method according to claim 9 wherein said insulating layer comprises SiO2.